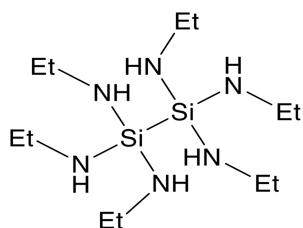
Catalog # 14-1955 Hexakis(ethylamino)disilane (99.995%-Si) PURATREM



Thermal Behavior:

- Melting point -7°C
- Boiling point 257°C

Technical Notes:

1. ALD precursor for Si thin film depositions.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiO_2	ALD	110°C	-	O_3	150-300°C	1
$Al_xSi_yO_z$	ALD	65°C	2.25 Torr	Me_3Al, D_2O	200°C	2
SiO_2-Fe_2O_3	ALD	65-67°C	-	$FeCl_3$, O_3	300°C	3

References:

1. *ECS Trans.* **2008**, *13*, 453.
2. *Chem. Mater.* **2012**, *24*, 3859.
3. *J. Vac. Sci. Technol. A*, **2020**, *38*, 042405.